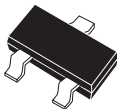


CMPD914**HIGH SPEED
SWITCHING DIODE****SOT-23 CASE**

CentralTM

Semiconductor Corp.

DESCRIPTION

The CENTRAL SEMICONDUCTOR CMPD914 type is a ultra-high speed silicon switching diode manufactured by the epitaxial planar process, in an epoxy molded surface mount package, designed for high speed switching applications.

Marking code is C5D.

MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$)

	SYMBOL		UNITS
Continuous Reverse Voltage	V_R	75	V
Peak Repetitive Reverse Voltage	V_{RRM}	100	V
Continuous Forward Current	I_F	250	mA
Peak Repetitive Forward Current	I_{FRM}	250	mA
Forward Surge Current, $t_p=1\ \mu\text{sec.}$	I_{FSM}	4000	mA
Forward Surge Current, $t_p=1\ \text{msec.}$	I_{FSM}	2000	mA
Forward Surge Current, $t_p=1\ \text{sec.}$	I_{FSM}	1000	mA
Power Dissipation	P_D	350	mW
Operating and Storage			
Junction Temperature	T_J, T_{stg}	-65 to +150	$^{\circ}\text{C}$
Thermal Resistance	θ_{JA}	357	$^{\circ}\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
V_{BR}	$I_R=100\ \mu\text{A}$	100		V
I_R	$V_R=20\text{V}$		25	nA
I_R	$V_R=75\text{V}$		5.0	μA
V_F	$I_F=10\text{mA}$		1.0	V
C_T	$V_R=0, f=1\ \text{MHz}$		4.0	pF
t_{rr}	$I_R=I_F=10\text{mA}, R_L=100\ \Omega, \text{Rec. to } 1.0\text{mA}$		4.0	ns

All dimensions in inches (mm).

